



SOLID STATE DEVICES, INC

PRELIMINARY

**SFF340M
SFF340Z**

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

Designer's Data Sheet

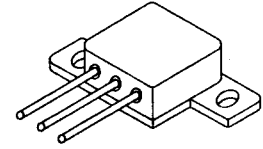
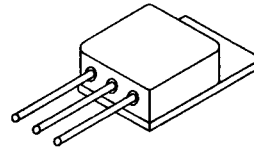
FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed package
- TX, TXV and Space Level screening available
- Replaces: IRFM340 Types

**10 AMP
400 VOLTS
0.55Ω
N-CHANNEL
POWER MOSFET**

TO-254

TO-254Z

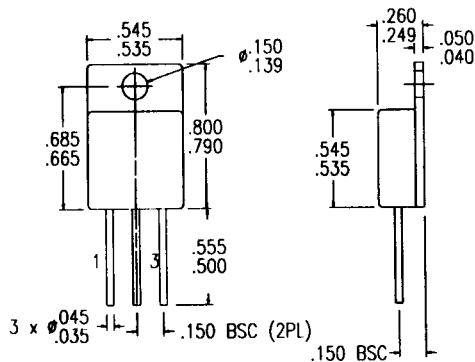


MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	400	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	8.5	Amps
Operating and Storage Temperature	Top & Tstg	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1.7	°C/W
Total Device Dissipation @ TC=25°C	P _D	79	Watts
Total Device Dissipation @ TC=55°C		55	

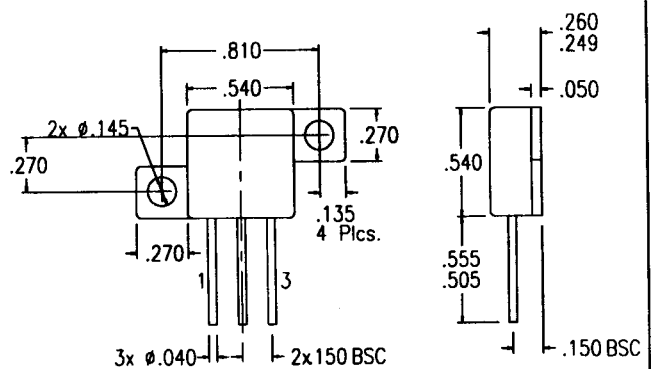
PACKAGE OUTLINE: TO-254

**PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE**



PACKAGE OUTLINE: TO-254Z

**PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE**



Available with Glass or Ceramic Seals. Contact Factory for details.

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00077 B

MED

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ELECTRICAL CHARACTERISTICS @ T_J=25 °C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250µA)		BVDSS	400	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID)		RDS(on)	---	0.42	0.55	Ω
On State Drain Current (VDS > ID(on) X RDS(on) Max, VGS=10 V)		ID(on)	10	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250µA)		VGS(th)	2.0	---	4.0	V
Forward Transconductance (VDS ≥ 50V, IDS=60% rated ID)		gfs	5.8	8.7	---	S(τ)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		IDSS	---	---	250 1000	µA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated VGS	IGSS	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	VGS=10 Volts 80% rated VDS ID=10A	Qg Qgs Qgd	---	43 6 22	65 9.3 33	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	VDD=50% rated VDS ID=10A RG=9.1Ω RD=20Ω	td(on) tr td(off) tf	---	14 27 50 24	9 30 74 36	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, TJ=25°C)		VSD	---	---	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	TJ=25°C IF=rated ID di/dt=100 A/µsec	t _{rr} QRR	170 1.6	370 3.8	790 8.2	nsec µC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	Ciss Coss Crss	---	1300 210 37	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.